

#### 20V N-Channel Enhancement Mode MOSFET

Voltage 20 V Current 500mA

#### **Features**

- Low Voltage Drive (1.2V).
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- ESD Protected
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

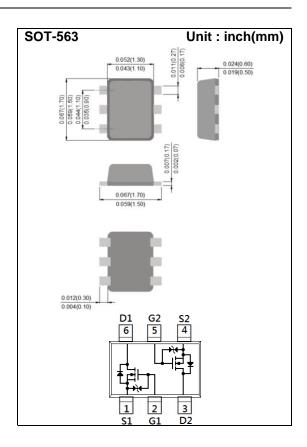
#### **Mechanical Data**

• Case: SOT-563 Package

Terminals : Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.0026 grams

Marking: X08



## **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	20	V
Gate-Source Voltage		V <sub>G</sub> s	<u>+</u> 10	V
Continuous Drain Current		ID	500	mA
Pulsed Drain Current		I <sub>DM</sub>	1000	mA
Power Dissipation	T <sub>A</sub> =25°C	DD	300	mW
	Derate above 25°C	PD	2.8	mW/°C
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C
Typical Thermal Resistance - Junction to Ambient <sup>(Note 3)</sup>		Reja	417	°C/W



## **Electrical Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V,I <sub>D</sub> =250uA	20	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250uA	0.3	0.64	0.9	V	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =500mA	-	310	400		
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =200mA	-	360	650	mΩ	
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =100mA	-	430	800		
		V <sub>GS</sub> =1.5V, I <sub>D</sub> =50mA	-	510	1200		
		V <sub>GS</sub> =1.2V, I <sub>D</sub> =20mA	-	710	3000		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =16V, V <sub>GS</sub> =0V	-	-	1	uA	
Gate-Source Leakage Current	Igss	V <sub>GS</sub> = <u>+</u> 8V, V <sub>DS</sub> =0V	-	<u>+</u> 0.5	<u>+</u> 10	uA	
Dynamic <sup>(Note 5)</sup>							
Total Gate Charge	Qg	V <sub>DS</sub> =10V, I <sub>D</sub> =500mA,	-	1.4	-	nC	
Gate-Source Charge	Qgs		-	0.22	-		
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>	-	0.21	-		
Input Capacitance	Ciss		-	67	-	pF	
Output Capacitance	Coss	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V,	-	19	-		
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	6	-		
Turn-On Delay Time	td <sub>(on)</sub>	V 40V L 450 A	-	2.8	-		
Turn-On Rise Time	tr	V <sub>DD</sub> =10V, I <sub>D</sub> =150mA,	-	20	-	ns	
Turn-Off Delay Time	td <sub>(off)</sub>	$V_{GS}=4.0V$ , $R_{G}=10\Omega^{(Note~1,2)}$	-	23	-		
Turn-Off Fall Time	tf	RG=1002(Note 1,2)	-	23	-		
Drain-Source Diode							
Maximum Continuous Drain-Source					500	m ^	
Diode Forward Current	Is		_	-	500	mA	
Diode Forward Voltage	V <sub>SD</sub>	Is=500mA, V <sub>GS</sub> =0V	-	0.87	1.3	٧	

#### NOTES:

- 1. Pulse width<300us, Duty cycle<2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.



#### **TYPICAL CHARACTERISTIC CURVES**

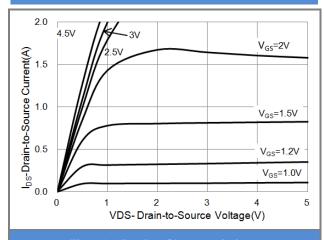
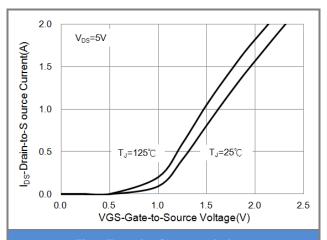


Fig.1 On-Region Characteristics



**Fig.2 Transfer Characteristics** 

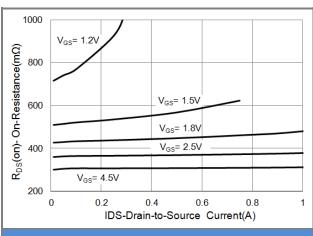


Fig.3 On-Resistance vs. Drain Current

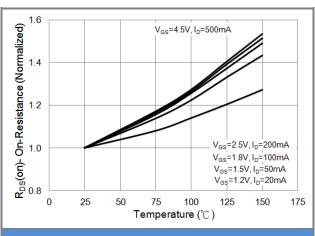
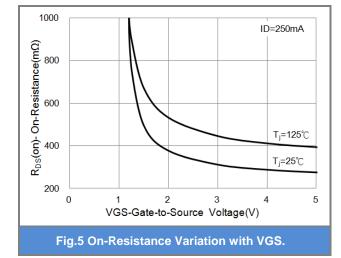
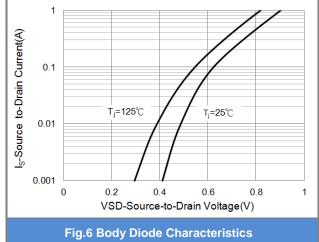


Fig.4 On-Resistance vs. Junction temperature







#### **TYPICAL CHARACTERISTIC CURVES**

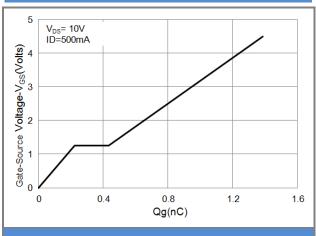


Fig.7 Gate-Charge Characteristics

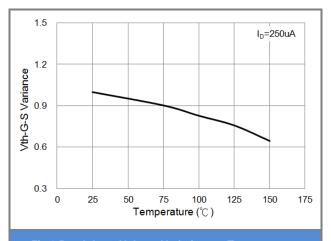


Fig.8 Breakdown Voltage Variation vs. Temperature

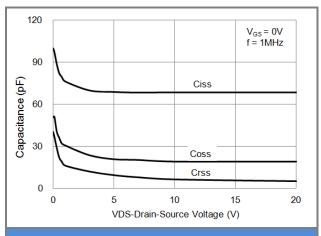


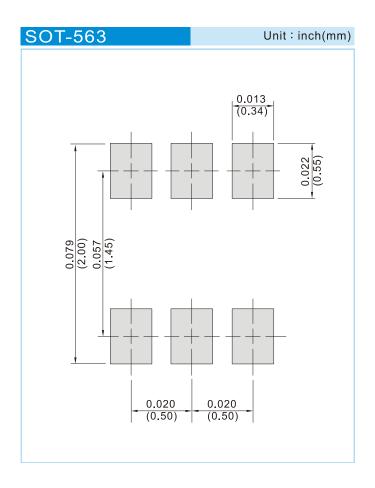
Fig.9 Threshold Voltage Variation with Temperature



# **Product and Packing Information**

Part No.	Package Type	Packing Type	Marking
PJX8808	SOT-563	4K pcs / 7" reel	X08
PJX8808	SOT-563	10K pcs / 13" reel	X08

## **Mounting Pad Layout**





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